L12 ANSWER 4 OF 4 CAPLUS COPYRIGHT 2004 ACS on STN
AN 2001:142245 CAPLUS
DN 134:200520
TI Multilayer **photoresist** material and resist pattern formation using it
IN Kanda, Yoshiki
PA Tokyo Ohka Kogyo Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 7 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

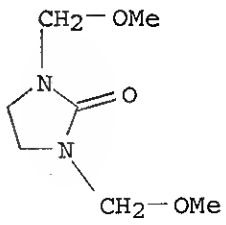
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2001056550	A2	20010227	JP 1999-234689	19990820
PRAI	JP 1999-234689		19990820		

DATE NOT GOOD ✓

AB The resist material comprises a substrate successively having (A) a dry-developable org. layer by O plasma and (B) a neg. **photoresist** layer contg. an alkali-sol. polymer with wt. av. mol. wt. 10,000-50,000, a compd. generating acid by irradn., and a crosslinking agent having .gtoreq.1 of hydroxyalkyl or lower alkoxyalkyl group. The resist pattern is formed by the steps of (1) selectively exposing and heat treating the neg. **photoresist layer**, (2) **silylation treatment** and **applying** O plasma resistance to the unexposed area, and (3) dry developing the exposed area of the neg. **photoresist** and the org. layer by O plasma using the unexposed area as a mask. Fine resist pattern without edge roughness is obtained.

IT **2669-72-9**, MX 280
RL: TEM (Technical or engineered material use); USES (Uses)
(MX 280; multilayer **photoresist** material comprising org. layer and neg. resist layer)

RN 2669-72-9 CAPLUS
CN 2-Imidazolidinone, 1,3-bis(methoxymethyl)- (6CI, 7CI, 8CI, 9CI) (CA INDEX NAME)



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09/638,872
8/15/00

L14 ANSWER 4 OF 18 CAPLUS COPYRIGHT 2004 ACS on STN
AN 2002:392164 CAPLUS
DN 136:409024
TI **Negative-working photoresist** composition for using in combination with organic antireflective coating
IN Tachikawa, Toshikazu; Kaneko, Fumitake; Kubota, Naotaka; Miyairi, Miwa; Hirosaki, Takako; Endo, Koutaro
PA Japan
SO U.S. Pat. Appl. Publ., 10 pp., Cont.-in-part of U.S. Ser. No. 638,872.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2002061467	A1	20020523	US 2002-53622	20020124
	JP 2001056555	A2	20010227	JP 1999-234688	19990820
	US 6406829	B1	20020618	US 2000-638872	20000815
PRAI	JP 1999-234688	A	19990820		
	US 2000-638872	A2	20000815		

parent of CIP

OS MARPAT 136:409024
AB Disclosed is a novel neg.-working chem.-amplification **photoresist** compn. comprising (A) an alkali-sol. resin, (B) an acid-generating agent and (C) a crosslinking agent, of which the component (B) is an onium salt compd. selected from the group consisting of iodonium salt compds. and sulfonium salt compds., having a specific fluoroalkyl sulfonate ion as the anionic moiety and the component (C) is a specific ethyleneurea compd. of the formula I (R1, R2 = hydroxyl, C1-4-alkoxy, R3, R4 = H, hydroxyl, C1-4-alkoxy). The **photoresist** compn. is particularly suitable for the formation of a **photoresist** layer on a substrate surface provided with an undercoating of a water-insol. org. anti-reflection film exhibiting excellent pattern resoln. and orthogonal cross sectional profile of the patterned resist layer with a good temp. latitude in the post-exposure baking treatment for latent image formation.
IT **2669-72-9**, MX 280
RL: TEM (Technical or engineered material use); USES (Uses)
(neg.-working chem.-amplification **photoresist** compn. for using in combination with org. antireflective coating)
RN 2669-72-9 CAPLUS
CN 2-Imidazolidinone, 1,3-bis(methoxymethyl)- (6CI, 7CI, 8CI, 9CI) (CA INDEX NAME)